

**Amendments to the Claims:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

**Listing of Claims:**

1. (Canceled)
2. (Canceled)
3. (Canceled)
4. (Canceled)
5. (Canceled)
6. (Canceled)
7. (Canceled)
8. (Canceled)
9. (Canceled)
10. (Canceled)
11. (Canceled)
12. (Canceled)
13. (Canceled)
14. (Canceled)
15. (Canceled)
16. (Canceled)
17. (Canceled)
18. (Previously presented) A method of forming a layer on a substrate in a

process chamber, the method comprising:

forming a fluorinated silicate glass layer over the substrate;

forming a patterned photoresist layer over the fluorinated silicate glass layer;

etching the fluorinated silicate glass layer according to the patterned photoresist

layer;

removing the photoresist layer and substantially simultaneously introducing nitrogen dopants into the fluorinated silicate glass layer by subjecting the photoresist layer and the fluorinated silicate glass layer to a plasma formed from a nitrogen-containing gas; wherein the plasma contains no oxygen species.

19. (Original) The method of claim 18 wherein the nitrogen-containing gas is selected from the group consisting of  $N_2$  and  $NH_3$ .

20. (Original) The method of claim 18 wherein the nitrogen-containing gas comprises at least one of  $N_2$  and  $NH_3$ .

21. (Canceled)

22. (Original) The method of claim 18 wherein nitrogen dopants are incorporated into the fluorinated silicate glass layer in a region near a surface of the fluorinated silicate glass layer which is exposed to the plasma formed from the nitrogen-containing gas.

23. (Original) The method of claim 22 wherein the region near the surface of the fluorinated silicate glass layer has a nitrogen content of less than about 10 at. %.

24. (Original) The method of claim 23 wherein the region near the surface of the fluorinated silicate glass layer has a nitrogen content of about 1 to about 5 at. %.

25. (Original) The method of claim 18 further comprising forming a barrier layer over the nitrogen-containing fluorinated silicate glass layer.

26. (Previously presented) The method of claim 25 wherein the barrier layer comprises at least one of silicon-carbon, silicon nitride, tantalum and tantalum nitride.

27. (Original) The method of claim 25 further comprising forming a metal layer over the barrier layer.

28. (Original) The method of claim 27 wherein the metal layer comprises copper.

29. (Canceled)

30. (Canceled)